

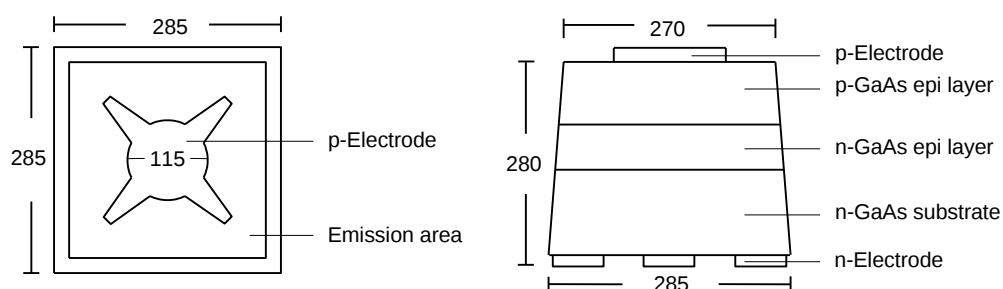
■ Features :

- GaAs/GaAs Wafer
- Good Spectral Matched to Si Detector

■ Typical Applications :

- Peripherals
- Photo Coupler
- Photo Interrupter

■ Outline Dimensions : (Unit: μm)



■ Physical Structure :

Chip dimension	Chip size	285 μm x 285 μm
	Thickness	280 μm
	Emission area	270 μm
	Bonding pad	115 μm
Electrode	Top: P (anode)	Aluminum (Gold optional)
	Backside: N (cathode)	Gold alloy
Surface condition	Smooth (Frosted for Gold pad)	

■ Electro-Optical Characteristics : ($T_a = 25^\circ\text{C}$)

Parameter	Symbol	Condition	Min.	Typ.	Max.	Unit
Forward Voltage	V_F	$I_F = 20 \text{ mA}$	-	1.23	1.45	V
		$I_F = 100 \text{ mA}$	-	1.44	-	
Reverse Voltage	V_R	$I_R = 10 \text{ uA}$	5	-	-	V
Wavelength	λ_p	$I_F = 20 \text{ mA}$	-	940	-	nm
Spectral width at half height	$\Delta\lambda$	$I_F = 20 \text{ mA}$	-	50	-	nm
Radiant Power	P_o	$I_F = 20 \text{ mA}$	0.20	-	-	mW

■ Typical Electro-Optical Characteristics Curve:

Fig 1. Forward Current vs. DC Forward Voltage

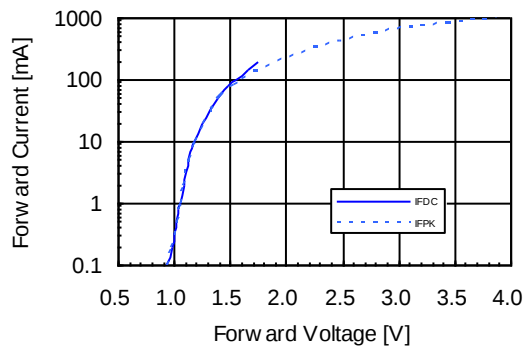


Fig 2. Relative Radiant Power vs. Wavelength

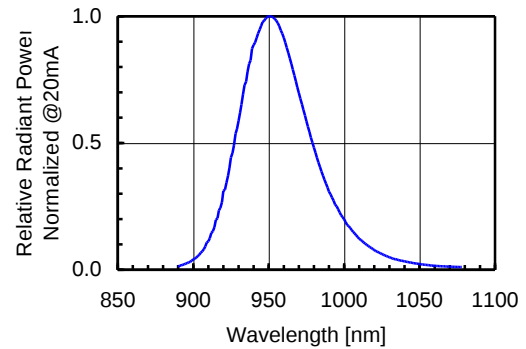
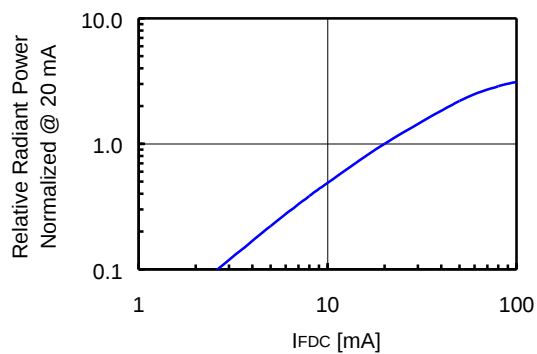
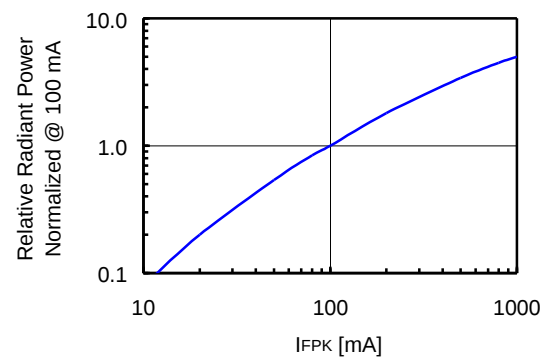
Fig 3. Relative Radiant Power
vs. Forward DC CurrentFig 4. Relative Radiant Power
Vs. Forward Peak Current

Fig 5. Forward DC Voltage vs. Temperature

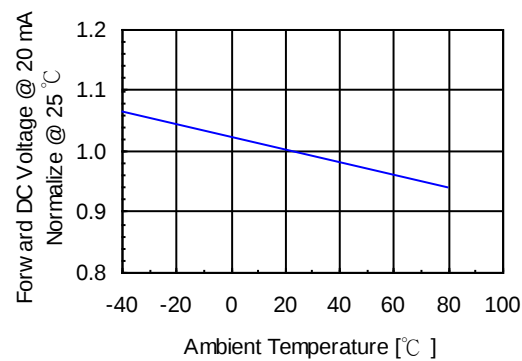


Fig 6. Relative Radiant Power vs. Temperature

